

TEM study of the early stages of Ti₂AlC oxidation at 900 °C

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The cross-sectional microstructure on Ti₂AlC oxidized for 1 h at 900 °C was investigated using focused ion beam/transmission electron microscopy. An Al-depleted intermediate layer formed between the oxide scale and the substrate that consisted of nonstoichiometric Ti₂Al_xC nanocrystallites. The oxide scale consisted of a TiO₂-rich outer layer and an Al₂O₃-rich inner layer. Ti₂AlC has been theoretically predicted to preserve its crystal structure down to a sub-stoichiometry of Ti₂Al_{0.5}C, and such a Ti₂Al_xC phase was observed in this study.

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Ti₂AlC is a promising material for various high-temperature applications, such as electrical heating elements [1], hot corrosion-resistant coatings [2], high-temperature electrodes [3] and cladding materials in lead-cooled fast nuclear reactors [4]. Ti₂AlC is a typical MAX phase [3,5] in the family of ternary compounds, with general formula M_{n+1}AX_n, where M is a transition metal, A is a group IIIA or IVA element, X is C or N, and *n* is from 1 to 3.

A major difficulty with non-oxide ceramics such as MAX phases is their tendency to oxidize in air. Understanding the oxidation behaviour of Ti₂AlC is critical for its application at elevated temperature in oxidizing atmospheres, and is also essential for the control of crack healing ability via surface oxidation [6,7]. The oxidation behaviour of Ti₂AlC has been investigated under isothermal conditions at high temperatures (1000–2000 °C) [8–10] and at intermediate temperatures (500–1000 °C) [11]. Parabolic oxidation kinetics have been observed by various researchers, and the growth of oxide scale on Ti₂AlC is believed to be caused by inward diffusion of O²⁻ and outward diffusion of Al³⁺ and Ti⁴⁺ [12,13]. The high-temperature oxidation resistance of Ti₂AlC involves selective oxidation of Al, leading to formation of continuous and protective Al₂O₃-rich scales [8–10,14]. After isothermal oxidation from 1100 to 1300 °C, a dense and continuous inner α-Al₂O₃ layer

and a discontinuous outer TiO₂ layer are formed [8–10]. At 1400 °C, a mixed outer layer of TiO₂ and Al₂TiO₅ and a cracked α-Al₂O₃ inner layer are formed [8,14]. The cracked oxide scale provides channels for rapid ingress of oxygen to the body, leading to heavy oxidation above 1400 °C [8].

There has been disagreement over the detail of the intermediate-temperature oxidation behaviour of Ti₂AlC, particularly that at 900 °C [8,15,16]. In our previous publication [8], X-ray diffraction (XRD), secondary electron imaging (SEI) and energy-dispersive spectroscopy (EDS) in a scanning electron microscope revealed that rutile TiO₂ was mainly present after 1 h of oxidation at 900 °C in air. Based on cross-sectional focused ion beam (FIB)/scanning electron microscopy (SEM) observation and thermodynamic arguments, Yang et al. [15] argue that a continuous Al₂O₃ layer (~250 nm thick) forms in the oxide scale on Ti₂AlC after 1 h of oxidation at 900 °C along with some large TiO₂ grains dispersed in the Al₂O₃ scale. Wang and Zhou [11] investigated the isothermal oxidation behaviour of Ti₂AlC at 500–900 °C by XRD, Raman spectroscopy and SEM, identifying transitional polymorphs of Al₂O₃ (γ-, δ-, θ- and α-) and TiO₂ (anatase and rutile) in the oxide scale. After 20 h of oxidation at 900 °C in air, the oxide scale formed is rutile TiO₂ and α-Al₂O₃ [11]. Reasons for these different observations likely include different as-made ceramic microstructures (such as grain size, porosity and impurity contents), and different oxidation temperatures and times used. These results

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do, however, demonstrate that the Ti_2AlC oxidation behaviour at 900°C is not fully understood. In all these studies, the oxide scale formed at 900°C is thin ($<1\ \mu\text{m}$) and nanosized grains are formed on the surface [8,11,15]. To fully understand the early stages of Ti_2AlC oxidation at 900°C , cross-sectional transmission electron microscopy (TEM), EDS and electron diffraction are necessary since only TEM investigations can provide all the structural, phase and crystallographic information of the materials down to atomistic levels [17]. The current work presents a detailed FIB/TEM examination of cross-sectional microstructures on Ti_2AlC oxidized for 1 h at 900°C .

Ti_2AlC samples were prepared by uniaxial hot-pressing Ti, Al and graphite starting materials at 1400°C for 1 h at 30 MPa in flowing Ar [18], and were supplied by Prof. Yanchun Zhou (Shenyang National Laboratory for Materials Science, Chinese Academy of Sciences). The as-received samples are predominantly single-phase Ti_2AlC ceramics as determined by XRD analysis, with densities of $4.10\ \text{g cm}^{-3}$ (99.8% theoretical) measured by the Archimedes method. The size of the lamellar grains in the Ti_2AlC ceramics is $\sim 50\text{--}100\ \mu\text{m}$ long, $\sim 3\text{--}10\ \mu\text{m}$ thick and $\sim 10\text{--}20\ \mu\text{m}$ wide. Ti_2AlC samples for oxidation experiments were cut by diamond saw to a size of $\sim 4 \times 4 \times 4\ \text{mm}^3$. The surfaces were ground to 1200 grit and polished to $1\ \mu\text{m}$, followed by degreasing in acetone. During oxidation experiments, samples were placed on a Pt crucible and heated to temperature at a rate of $20^\circ\text{C min}^{-1}$ in an open hearth furnace. Isothermal oxidation runs were performed for 1 h at 900°C in air before samples were removed and air cooled. Sections, $100\ \text{nm}$ thick, were then prepared for TEM using the in situ lift-out technique on a dual-beam FIB instrument (FEI Helios 600 NanoLab, FEI Company, Aachen, Eindhoven, The Netherlands). During FIB section preparation, a Pt protective layer was deposited to protect the feature of interest from Ga^+ milling, then a cross-section was in situ lifted-out and attached to a support grid that fits into a TEM specimen holder. TEM was carried out with an electron microscope operated at 200 kV (JEM 2000FX, JEOL Ltd., Tokyo, Japan) and a high-resolution electron microscope operated at 200 kV (JEM 2100, JEOL Ltd., Tokyo, Japan). Microstructures were examined in the TEM using bright-field (BF) and selected area electron diffraction (SAED) crystallographic analysis (operated using a double-tilt holder). The aperture size used for the selected area diffraction patterns is 200–300 nm. The diffraction patterns were solved using the SingleCrystal software (Crystal-Maker Software Ltd., Yarnton, Oxfordshire, UK). EDS chemical analysis in the JEM 2000 was performed using an ultrathin window detector (Oxford Instruments INCA, Oxford, UK). An electron-beam probe of $<10\ \text{nm}$ diameter was obtained in this instrument for EDS chemical analysis.

Figure 1a shows typical plan view surface morphology of the oxide scale formed after 1 h of oxidation at 900°C . The EDS analysis indicates that the small ($<1\ \mu\text{m}$) grains were composed of titanium and aluminium oxides. The rectangular frame in Figure 1a shows the region where a Pt protective layer was deposited and then the cross-sectional lamina was in situ lifted-

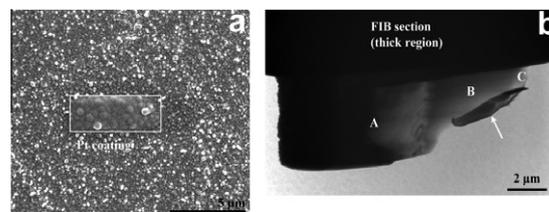


Figure 1. (a) Plan view of the surface morphology (SEI taken from FIB) of Ti_2AlC oxidized for 1 h at 900°C . The rectangular frame indicates the region where a Pt protective layer was deposited and then the cross-sectional lamina was lifted out. (b) Low-magnification BF-TEM image showing a cross-section of Ti_2AlC oxidized for 1 h at 900°C . A: Ti_2AlC substrate; B: intermediate layer; C: oxide scale. The arrowed region is a thin bent layer caused by Ga^+ milling during FIB.

out for TEM observations. Figure 1b is a low-magnification BF-TEM image of the cross-section of Ti_2AlC oxidized for 1 h at 900°C . The arrowed region in Figure 1b is a thin bent layer caused by Ga^+ milling during FIB. As revealed by EDS and SAED, the cross-section consisted of three parts (from the left to right): Ti_2AlC substrate (A), intermediate layer (B) and oxide scale (C).

An enlarged view of the A/B interface is shown in Figure 2a. A SAED pattern from A (Fig. 2b) indexed as Ti_2AlC [0001]. A ring pattern from B (Fig. 2c) also indexed as polycrystalline $\text{Ti}_2\text{Al}_x\text{C}$ structure (space group $P6_3/mmc$, ICDD 29-0095). EDS from A (not shown) suggests that the Ti/Al ratio is close to 2. EDS from B (not shown), however, indicates that it is close to 4. The combined SAED and EDS results indicate the intermediate layer B is likely to be nonstoichiometric $\text{Ti}_2\text{Al}_x\text{C}$ ($x < 1$). High-resolution TEM (HRTEM; Fig. 2d) revealed nanocrystallites ($<20\ \text{nm}$) distributed in the intermediate layer B. A typical fringe periodicity is $1.30\ \text{nm}$ (arrowed in Fig. 2d), coinciding with the the-

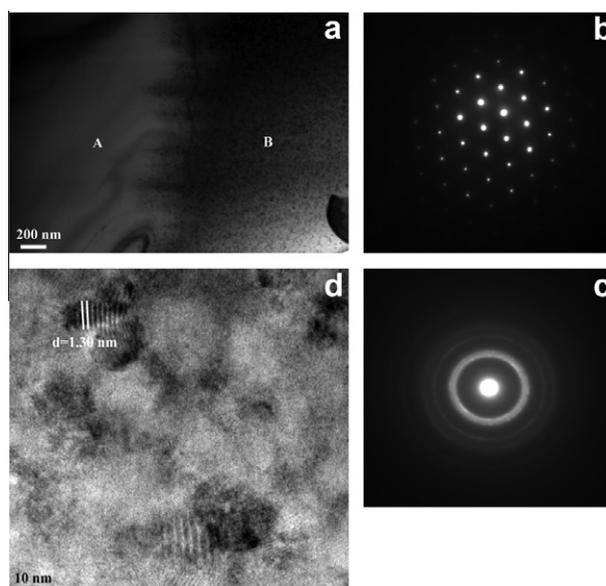


Figure 2. (a) An enlarged view of the A/B interface in Figure 1b. A: Ti_2AlC substrate; B: intermediate layer. (b) SAED pattern from A, indexed as Ti_2AlC [0001]. (c) SAED pattern from B, indexed as polycrystalline $\text{Ti}_2\text{Al}_x\text{C}$. (d) HRTEM image of intermediate layer B, revealing $\text{Ti}_2\text{Al}_x\text{C}$ nanocrystallites ($<20\ \text{nm}$).

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